Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	13	TOLCHINSKY-P TOLCHINSKY-PETER TOLCHINSKY-PETER-G	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/15 12:56
L2	1	(porous near2 silicon) with (substrate wafer) with (support near1 (substrate layer)) with (silicon near1 layer) with (device near1 layer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/15 12:59
L3	0	(porous near2 silicon) with (substrate wafer) with (support near1 (substrate layer)) with (silicon near1 layer) with (device near1 layer) with (removing splitting)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/15 12:58
L4	2	(porous near2 silicon) same (substrate wafer) same ((support temporary) near1 (substrate layer)) same (silicon near1 layer) same (device near1 layer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/15 13:01
L5	57	(porous near2 silicon) and (substrate wafer) and ((support temporary) near1 (substrate layer)) and (silicon near1 layer) and (device near1 layer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/15 14:21
L6	59	(porous near3 silicon) and (substrate wafer) and ((support temporary) near1 (substrate layer)) and (silicon near1 layer) and (device near1 layer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/15 14:43
L7	2	(porous with silicon) same (substrate wafer) same ((support temporary) near1 (substrate layer)) same ((silicon near1 layer) wafer) same (device near1 layer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/15 14:45